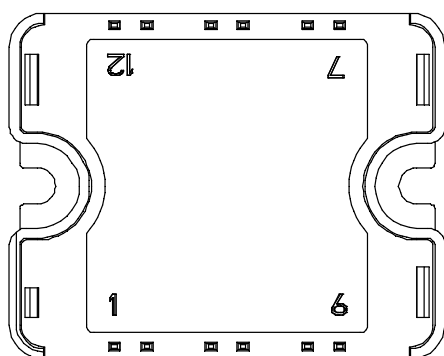
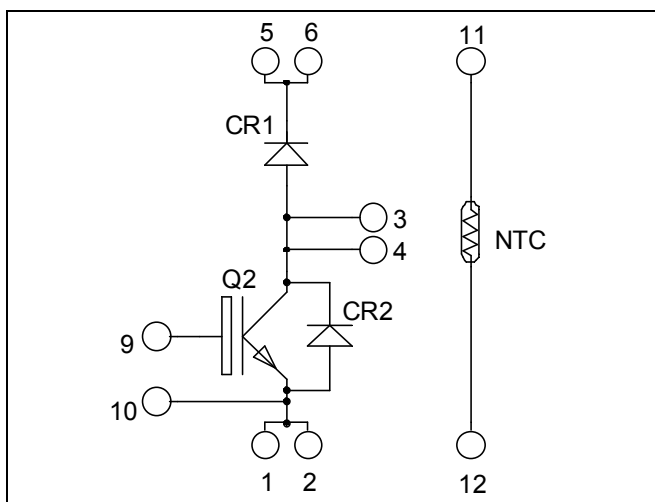


**Boost chopper  
Trench + Field Stop IGBT4  
Power module**

**$V_{CES} = 1200V$   
 $I_C = 90A @ T_c = 80^\circ C$**



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

## Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

## Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

## Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

## Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings         | Unit         |
|-----------|---------------------------------------|---------------------|--------------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 1200                | V            |
| $I_C$     | Continuous Collector Current          | $T_c = 25^\circ C$  | 110          |
|           |                                       | $T_c = 80^\circ C$  | 90           |
| $I_{CM}$  | Pulsed Collector Current              | $T_c = 25^\circ C$  | 150          |
| $V_{GE}$  | Gate - Emitter Voltage                | $\pm 20$            | V            |
| $P_D$     | Maximum Power Dissipation             | $T_c = 25^\circ C$  | 385          |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 150^\circ C$ | 150A @ 1150V |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

### Electrical Characteristics

| Symbol        | Characteristic                       | Test Conditions               | Min | Typ                                                   | Max          | Unit    |
|---------------|--------------------------------------|-------------------------------|-----|-------------------------------------------------------|--------------|---------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 1200V$ |     |                                                       | 250          | $\mu A$ |
| $V_{CE(sat)}$ | Collector Emitter saturation Voltage | $V_{GE} = 15V$<br>$I_C = 75A$ |     | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 1.85<br>2.25 | V       |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 3mA$  | 5.0 | 5.8                                                   | 6.5          | V       |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$   |     |                                                       | 600          | nA      |

### Dynamic Characteristics

| Symbol       | Characteristic               | Test Conditions                                                                                                           | Min                                                   | Typ        | Max | Unit    |
|--------------|------------------------------|---------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------|------------|-----|---------|
| $C_{ies}$    | Input Capacitance            | $V_{GE} = 0V$                                                                                                             |                                                       | 4.4        |     | nF      |
| $C_{oes}$    | Output Capacitance           | $V_{CE} = 25V$                                                                                                            |                                                       | 0.29       |     |         |
| $C_{res}$    | Reverse Transfer Capacitance | $f = 1MHz$                                                                                                                |                                                       | 0.24       |     |         |
| $Q_G$        | Gate charge                  | $V_{GE} = \pm 15V; V_{CE} = 600V$<br>$I_C = 75A$                                                                          |                                                       | 0.57       |     | $\mu C$ |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $25^\circ\text{C}$ )<br>$V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 75A$<br>$R_G = 2.2\Omega$  |                                                       | 130        |     | ns      |
| $T_r$        | Rise Time                    |                                                                                                                           |                                                       | 20         |     |         |
| $T_{d(off)}$ | Turn-off Delay Time          |                                                                                                                           |                                                       | 300        |     |         |
| $T_f$        | Fall Time                    |                                                                                                                           |                                                       | 45         |     |         |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $150^\circ\text{C}$ )<br>$V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 75A$<br>$R_G = 2.2\Omega$ |                                                       | 150        |     | ns      |
| $T_r$        | Rise Time                    |                                                                                                                           |                                                       | 35         |     |         |
| $T_{d(off)}$ | Turn-off Delay Time          |                                                                                                                           |                                                       | 350        |     |         |
| $T_f$        | Fall Time                    |                                                                                                                           |                                                       | 80         |     |         |
| $E_{on}$     | Turn-on Switching Energy     | $V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 75A$                                                                     | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 3.4<br>8.5 |     | mJ      |
| $E_{off}$    | Turn-off Switching Energy    | $R_G = 2.2\Omega$                                                                                                         | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 4.2<br>7.2 |     | mJ      |
| $I_{sc}$     | Short Circuit data           | $V_{GE} \leq 15V; V_{Bus} = 900V$<br>$t_p \leq 10\mu s; T_j = 150^\circ\text{C}$                                          |                                                       | 300        |     | A       |

### Chopper diode ratings and characteristics

| Symbol    | Characteristic                          | Test Conditions                                      | Min                                                   | Typ         | Max | Unit    |
|-----------|-----------------------------------------|------------------------------------------------------|-------------------------------------------------------|-------------|-----|---------|
| $V_{RRM}$ | Maximum Peak Repetitive Reverse Voltage |                                                      | 1200                                                  |             |     | V       |
| $I_{RM}$  | Maximum Reverse Leakage Current         | $V_R = 1200V$                                        |                                                       |             | 250 | $\mu A$ |
| $I_F$     | DC Forward Current                      |                                                      |                                                       | 90          |     | A       |
| $V_F$     | Diode Forward Voltage                   | $I_F = 75A$<br>$V_{GE} = 0V$                         | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 1.7<br>1.65 | 2.2 | V       |
| $t_{rr}$  | Reverse Recovery Time                   | $I_F = 75A$<br>$V_R = 600V$<br>$di/dt = 1900A/\mu s$ | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 155<br>300  |     | ns      |
| $Q_{rr}$  | Reverse Recovery Charge                 |                                                      | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 7.3<br>15.2 |     | $\mu C$ |
| $E_r$     | Reverse Recovery Energy                 |                                                      | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ | 2.6<br>5.5  |     | mJ      |

## Thermal and package characteristics

| Symbol            | Characteristic                                               |             |    | Min   | Typ | Max  | Unit |
|-------------------|--------------------------------------------------------------|-------------|----|-------|-----|------|------|
| R <sub>thJC</sub> | Junction to Case Thermal Resistance                          |             |    | IGBT  |     | 0.39 | °C/W |
|                   |                                                              |             |    | Diode |     | 0.62 |      |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz |             |    | 4000  |     |      | V    |
| T <sub>J</sub>    | Operating junction temperature range                         |             |    | -40   |     | 175  | °C   |
| T <sub>STG</sub>  | Storage Temperature Range                                    |             |    | -40   |     | 125  |      |
| T <sub>C</sub>    | Operating Case Temperature                                   |             |    | -40   |     | 100  |      |
| Torque            | Mounting torque                                              | To heatsink | M4 | 2     |     | 3    | N.m  |
| Wt                | Package Weight                                               |             |    |       |     | 80   | g    |

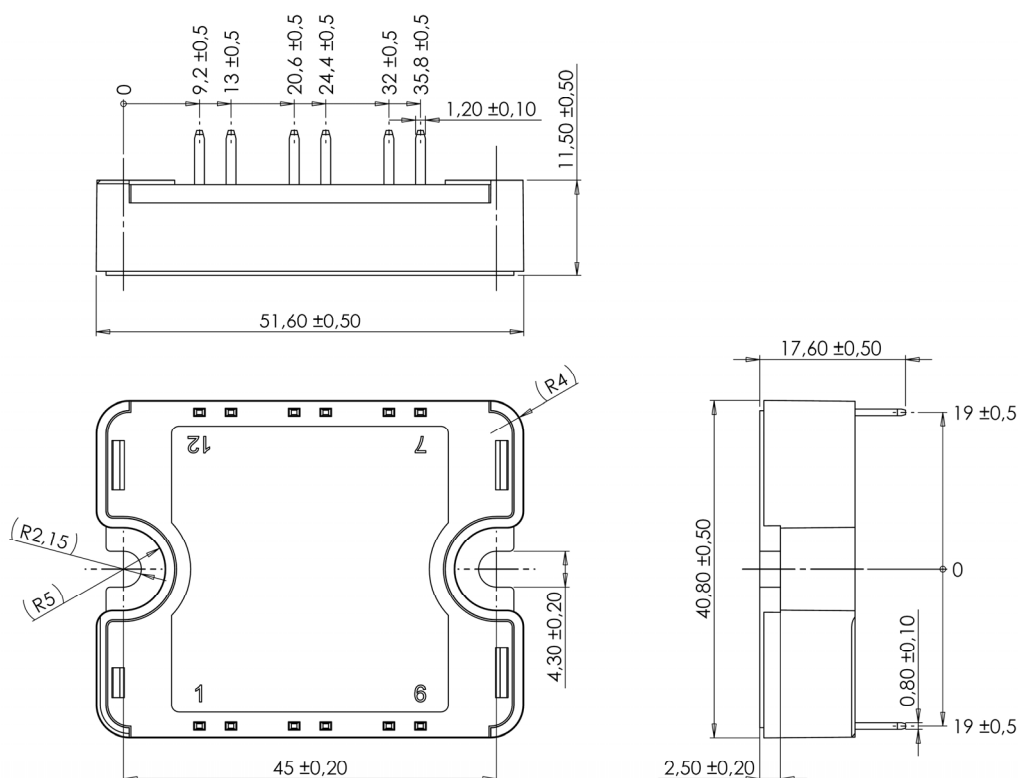
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol                            | Characteristic             | Min | Typ  | Max | Unit |
|-----------------------------------|----------------------------|-----|------|-----|------|
| R <sub>25</sub>                   | Resistance @ 25°C          |     | 50   |     | kΩ   |
| ΔR <sub>25</sub> /R <sub>25</sub> |                            |     | 5    |     | %    |
| B <sub>25/85</sub>                | T <sub>25</sub> = 298.15 K |     | 3952 |     | K    |
| ΔB/B                              | T <sub>C</sub> = 100°C     |     | 4    |     | %    |

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

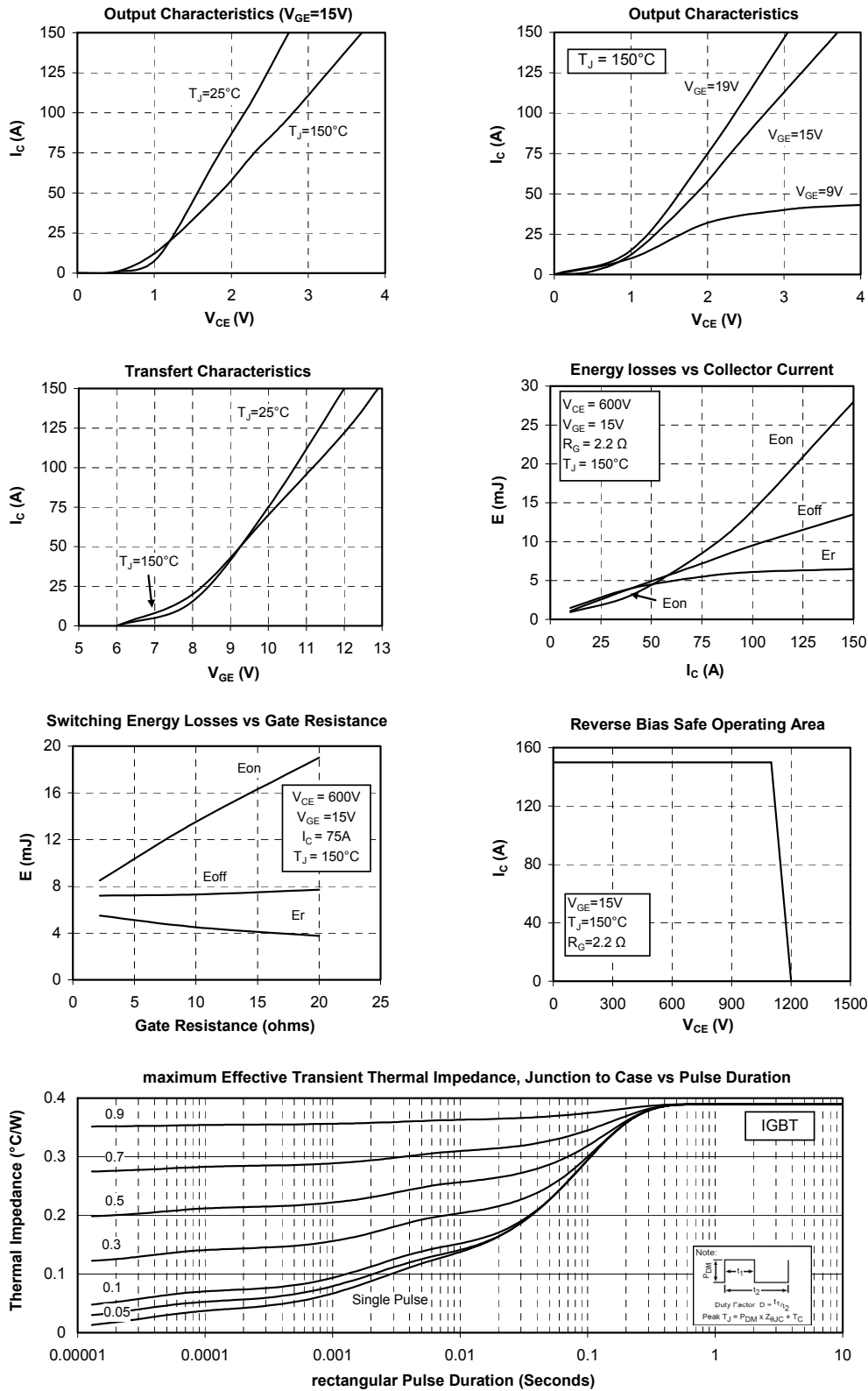
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

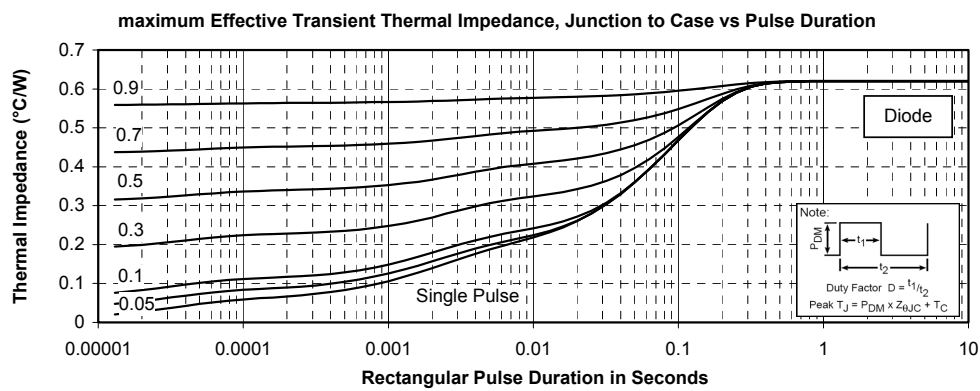
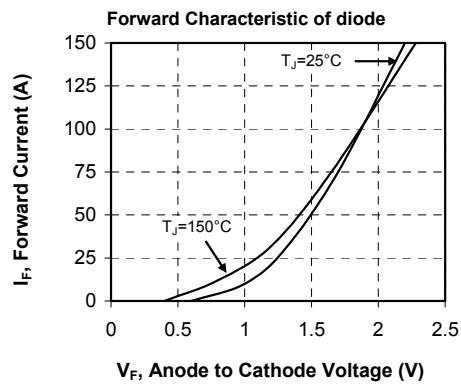
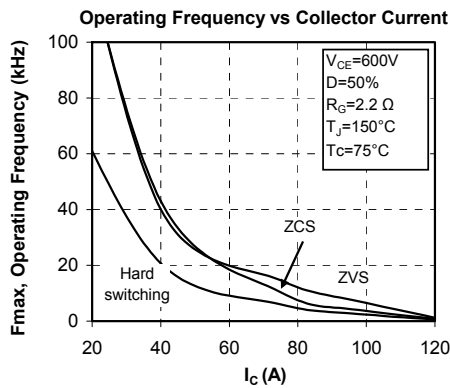
## SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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